


19. (Newly Added) The thin film deposition reactor of claim 18, wherein the interval between the center of the diffusion plate and the wafer block is larger than the interval between the edges of the diffusion plate and the wafer block to adjust a thickness, purity and electrical characteristics of a deposited thin film.

 *concave*

*B1*  
*cont*  
20. (Newly Added) The thin film deposition reactor of claim 18, wherein the interval between the center of the diffusion plate and the wafer block is smaller than the interval between the edges of the diffusion plate and the wafer block to adjust a thickness, purity and electrical characteristics of a deposited thin film.

 *convex*